

阅读申明

- 1.本站收集的数据手册和产品资料都来自互联网，版权归原作者所有。如读者和版权方有任何异议请及时告之，我们将妥善解决。
- 2.本站提供的中文数据手册是英文数据手册的中文翻译，其目的是协助用户阅读，该译文无法自动跟随原稿更新，同时也可能存在翻译上的不当。建议读者以英文原稿为参考以便获得更精准的信息。
- 3.本站提供的产品资料，来自厂商的技术支持或者使用者的心得体会等，其内容可能存在描述上的差异，建议读者做出适当判断。
- 4.如需与我们联系，请发邮件到marketing@iczoom.com，主题请标有“数据手册”字样。

Read Statement

1. The datasheets and other product information on the site are all from network reference or other public materials, and the copyright belongs to the original author and original published source. If readers and copyright owners have any objections, please contact us and we will deal with it in a timely manner.
2. The Chinese datasheets provided on the website is a Chinese translation of the English datasheets. Its purpose is for reader's learning exchange only and do not involve commercial purposes. The translation cannot be automatically updated with the original manuscript, and there may also be improper translations. Readers are advised to use the English manuscript as a reference for more accurate information.
3. All product information provided on the website refer to solutions from manufacturers' technical support or users the contents may have differences in description, and readers are advised to take the original article as the standard.
4. If you have any questions, please contact us at marketing@iczoom.com and mark the subject with "Datasheets" .



EFC4619R

Power MOSFET 24V, 6A, 23mΩ N-Channel Dual EFCP

ON Semiconductor®

<http://onsemi.com>

Features

- 2.5V drive
- Common-drain type
- 2KV ESD HBM
- Protection diode in
- Halogen free compliance

Applications

- Lithium-ion battery charging and discharging switch

Specifications

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

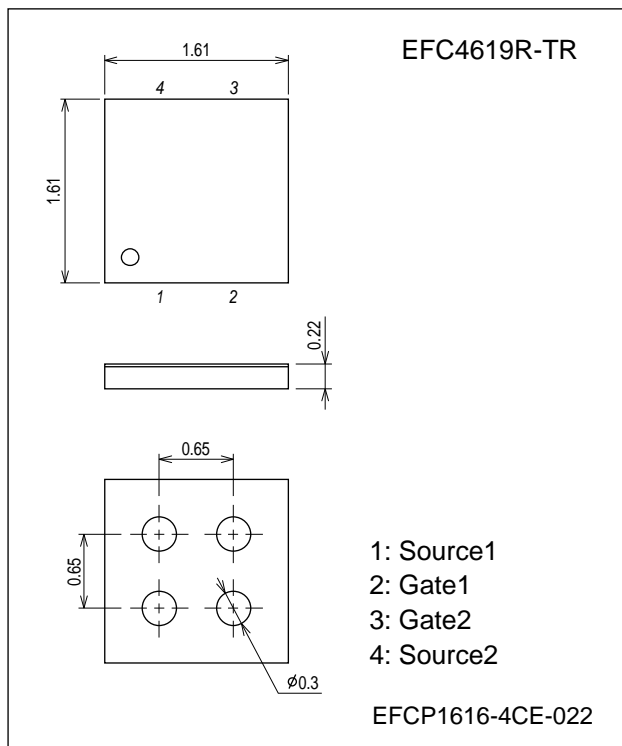
Parameter	Symbol	Conditions	Ratings	Unit
Source to Source Voltage	V_{SSS}		24	V
Gate to Source Voltage	V_{GSS}		± 12	V
Source Current (DC)	I_S		6	A
Source Current (Pulse)	I_{SP}	$PW \leq 10\mu\text{s}$, duty cycle $\leq 1\%$	60	A
Total Dissipation	P_T	When mounted on ceramic substrate (5000mm ² ×0.8mm)	1.6	W
Channel Temperature	T_{ch}		150	°C
Storage Temperature	T_{stg}		-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

unit : mm (typ)

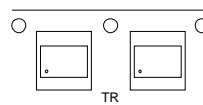
7074



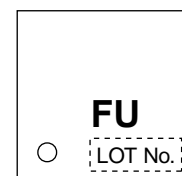
Ordering & Package Information

Device	Package	Shipping	note
EFC4619R-TR	EFCP	5000 pcs. / reel	Pb-Free and Halogen-Free

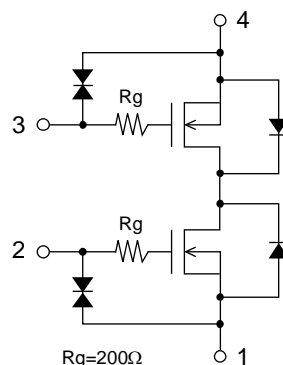
Packing Type: TR



Marking



Electrical Connection



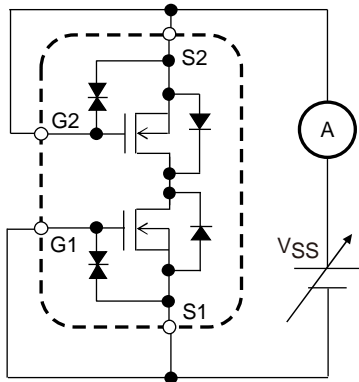
EFC4619R

Electrical Characteristics at Ta = 25°C

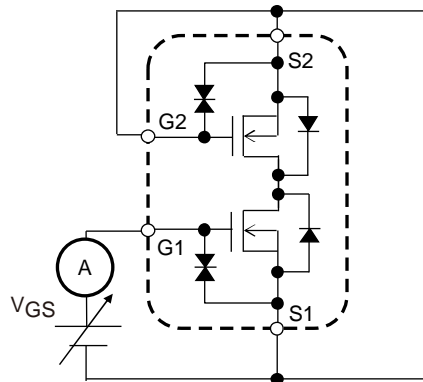
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Source to Source Breakdown Voltage	V(BR) _{SSS}	I _S =1mA, V _{GS} =0V Test Circuit 1	24			V
Zero-Gate Voltage Source Current	I _{SSS}	V _{SS} =20V, V _{GS} =0V Test Circuit 1			1	μA
Gate to Source Leakage Current	I _{GSS}	V _{GS} =±8V, V _{SS} =0V Test Circuit 2			±1	μA
Cutoff Voltage	V _{GS(off)}	V _{SS} =10V, I _S =1mA Test Circuit 3	0.5		1.3	V
Forward Transfer Admittance	y _{fs}	V _{SS} =10V, I _S =3A Test Circuit 4		5.8		S
Static Source to Source On-State Resistance	R _{SS(on)1}	I _S =3A, V _{GS} =4.5V Test Circuit 5	13.5	19.8	23	mΩ
	R _{SS(on)2}	I _S =3A, V _{GS} =4.0V Test Circuit 5	14	20.5	24	mΩ
	R _{SS(on)3}	I _S =3A, V _{GS} =3.7V Test Circuit 5	14.5	21	25.5	mΩ
	R _{SS(on)4}	I _S =3A, V _{GS} =3.1V Test Circuit 5	14.9	23	30	mΩ
	R _{SS(on)5}	I _S =3A, V _{GS} =2.5V Test Circuit 5	18.5	27	35	mΩ
Turn-ON Delay Time	t _{d(on)}	V _{SS} =10V, V _{GS} =4.5V, I _S =3A Test Circuit 7		340		ns
Rise Time	t _r			440		ns
Turn-OFF Delay Time	t _{d(off)}			24400		ns
Fall Time	t _f			22400		ns
Total Gate Charge	Q _g		V _{SS} =10V, V _{GS} =4.5V, I _S =6A Test Circuit 8		21.7	
Forward Source to Source Voltage	V _{F(S-S)}	I _S =3A, V _{GS} =0V Test Circuit 6		0.8	1.2	V

Test circuits are example of measuring FET1 side

Test Circuit 1
I_{SSS}

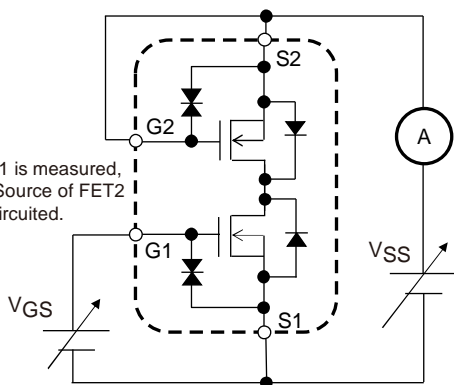


Test Circuit 2
I_{GSS}



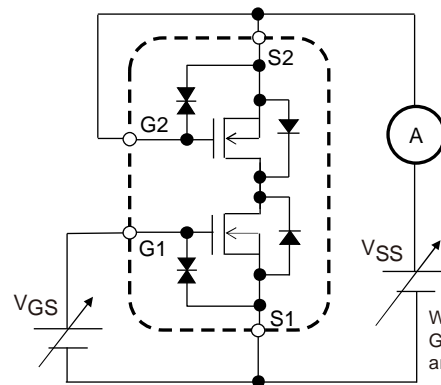
When FET1 is measured, Gate and Source of FET2 are short-circuited.

Test Circuit 3
V_{GS(off)}



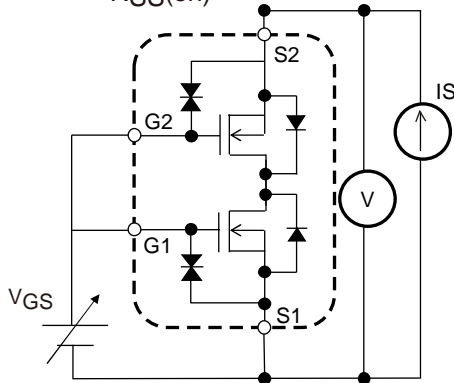
When FET1 is measured, Gate and Source of FET2 are short-circuited.

Test Circuit 4
|y_{fs}|

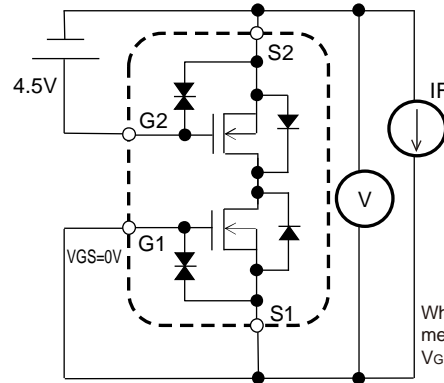


When FET1 is measured, Gate and Source of FET2 are short-circuited.

Test Circuit 5
R_{SS(on)}

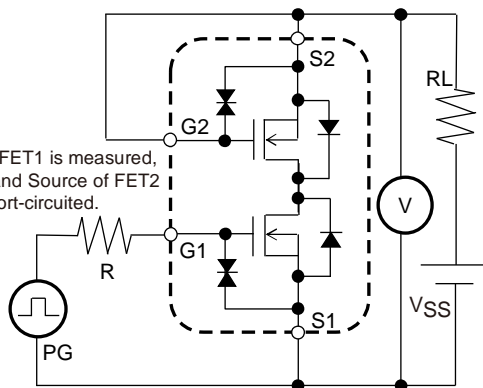


Test Circuit 6
V_{F(S-S)}



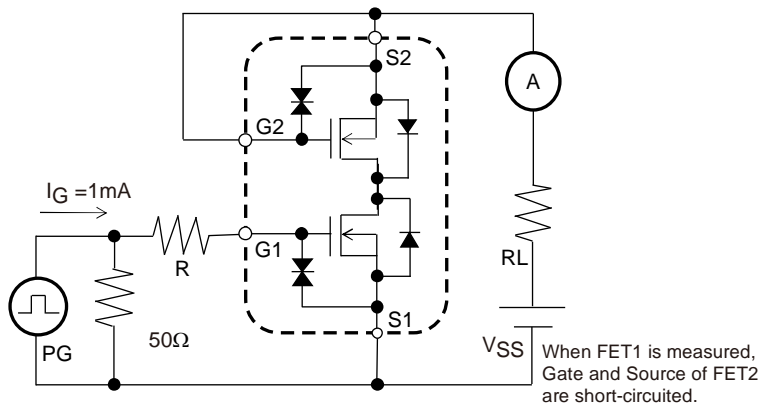
When FET1 is measured, +4.5V is added to V_{GS} of FET2.

Test Circuit 7
t_{d(on)}, t_r, t_{d(off)}, t_f



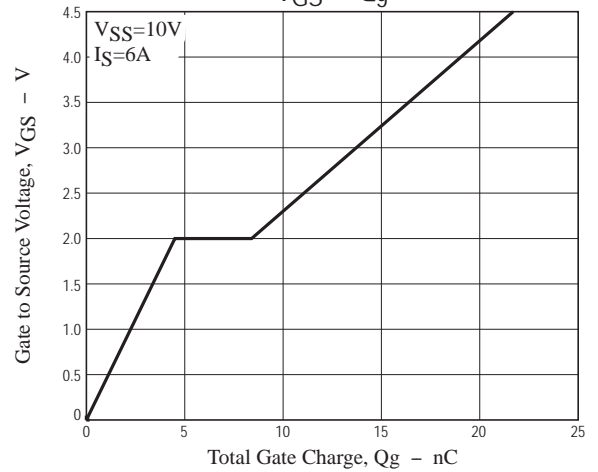
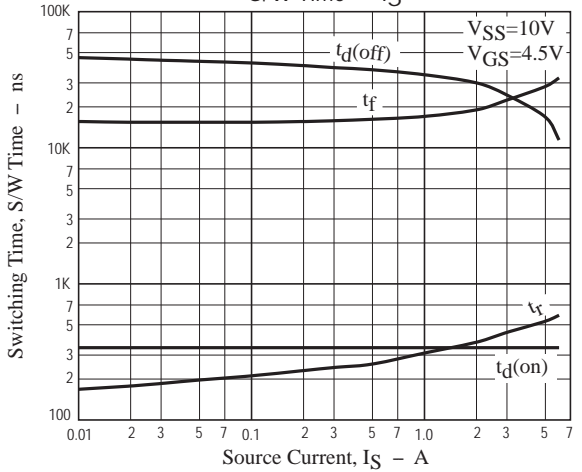
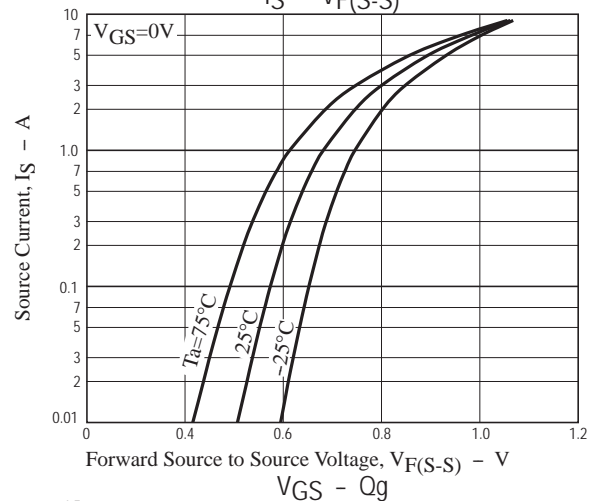
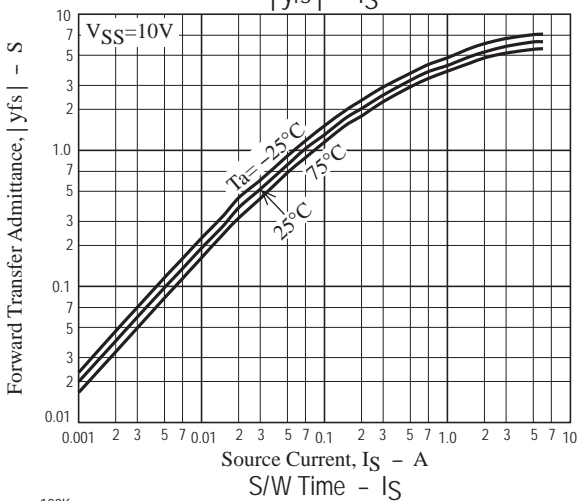
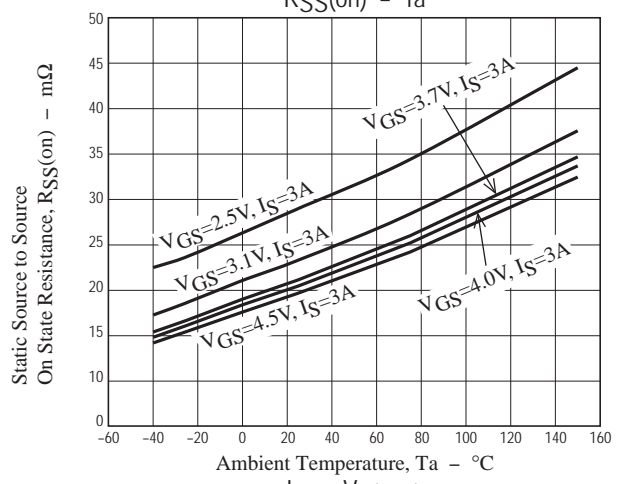
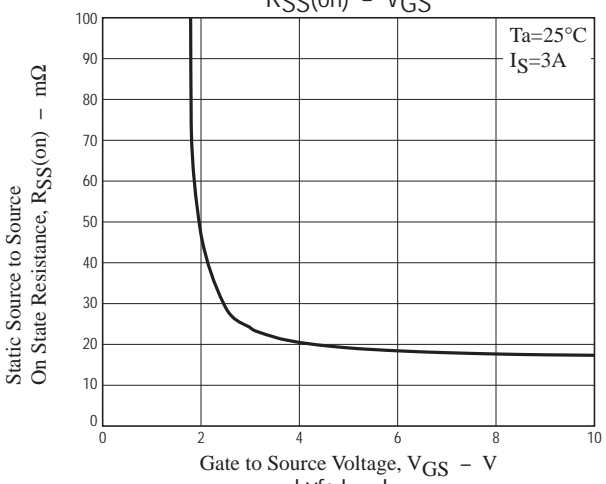
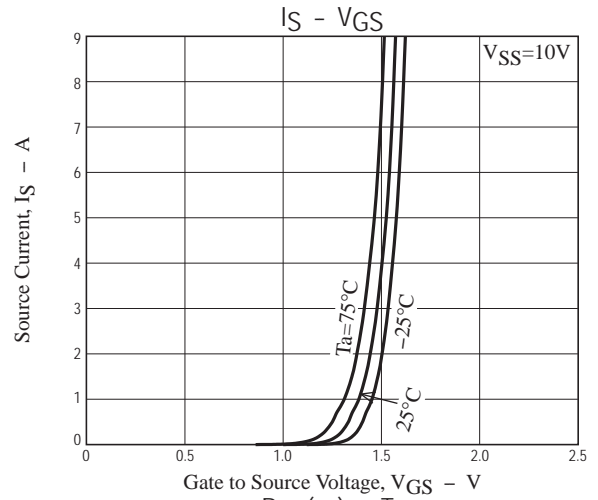
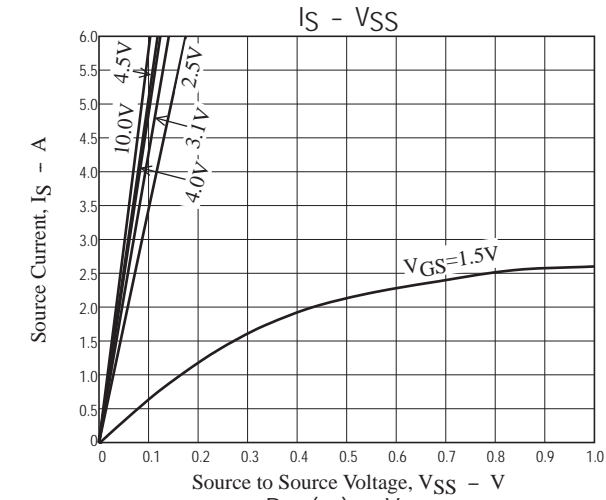
When FET1 is measured, Gate and Source of FET2 are short-circuited.

Test Circuit 8
Q_g

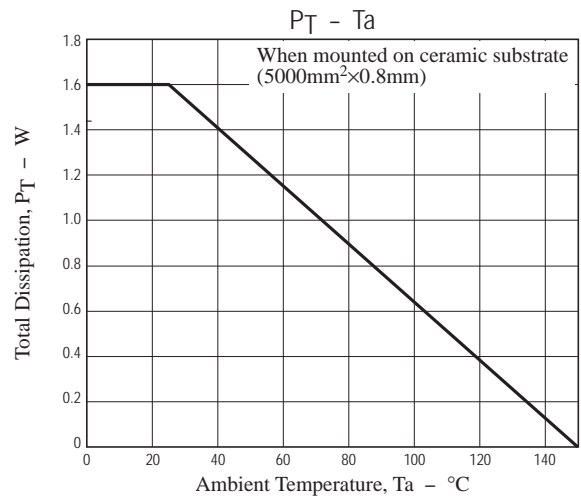
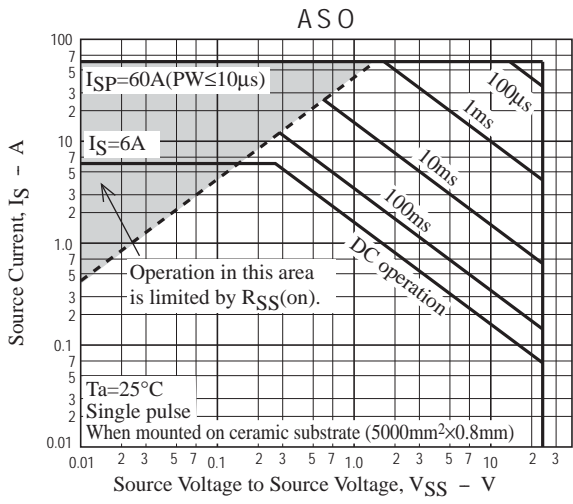


When FET1 is measured, Gate and Source of FET2 are short-circuited.

EFC4619R



EFC4619R



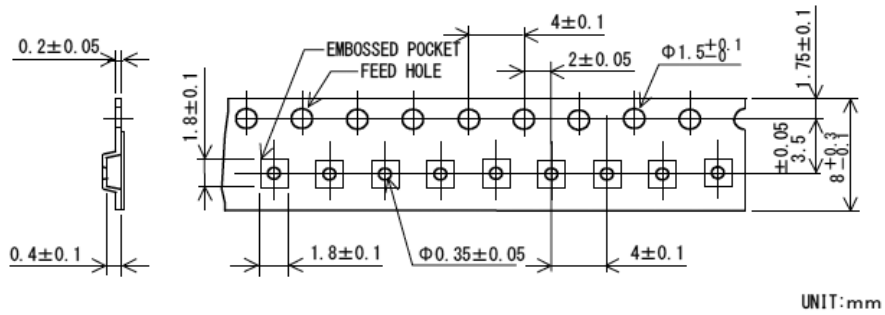
EFC4619R

Taping Specification

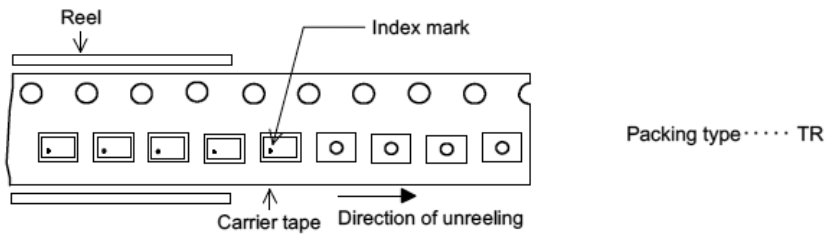
EFC4619R-TR

1. Taping Configuration

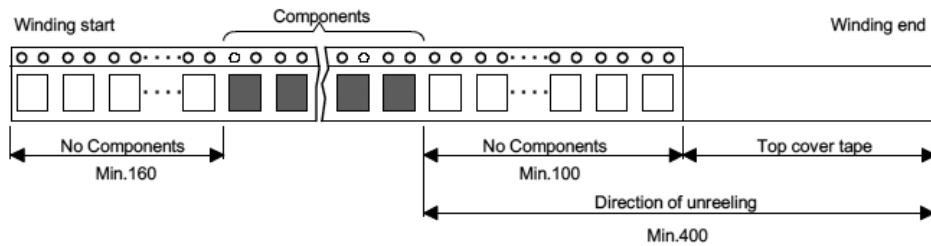
1-1. Carrier Tape Size (unit:mm)



1-2. Device Placement Direction



1-3. Leader portion and Trailer portion (unit:mm)

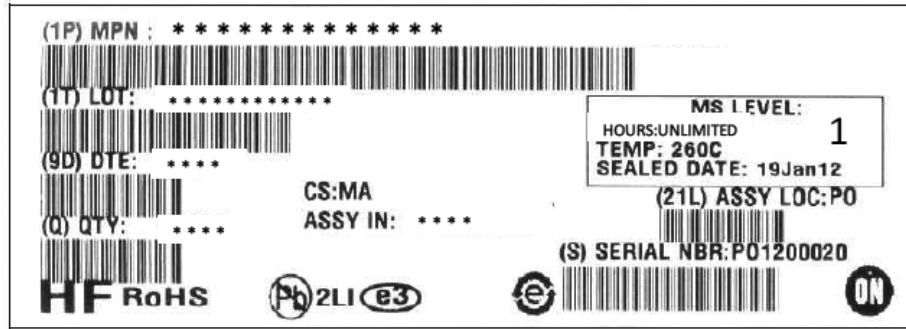


EFC4619R

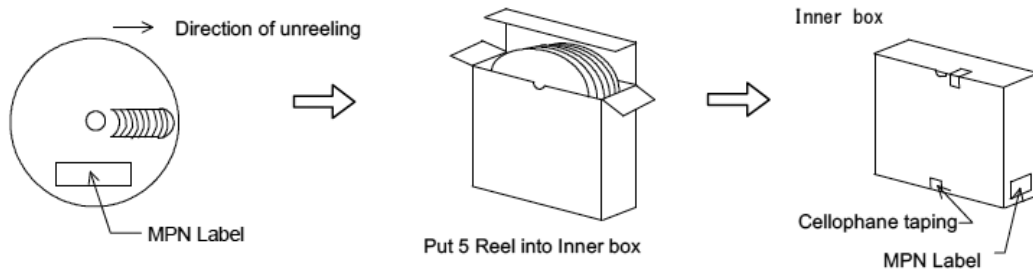
Packing Format

Carrier Tape code	Package code	Maximum Number of devices contained. (pcs.)			Packing Format	
		Reel	Inner box		Inner box BOX(C-1)	
1818X04	EFCP1616-4CE-022	5,000	25,000		5reels contained. Dimensions:mm 183×72×185	

MPN Label



Packing Method

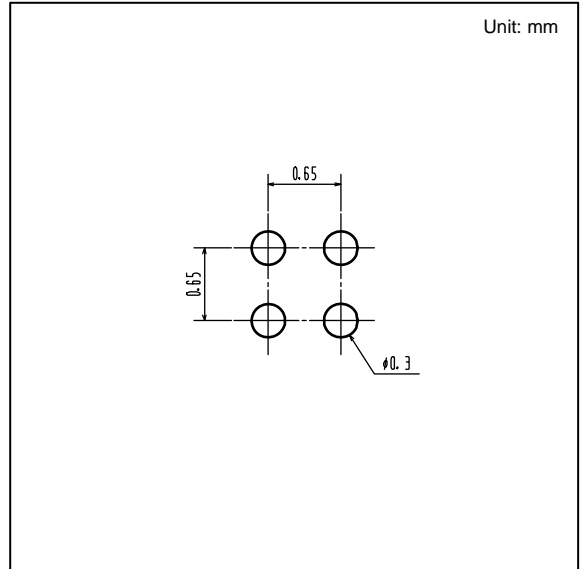
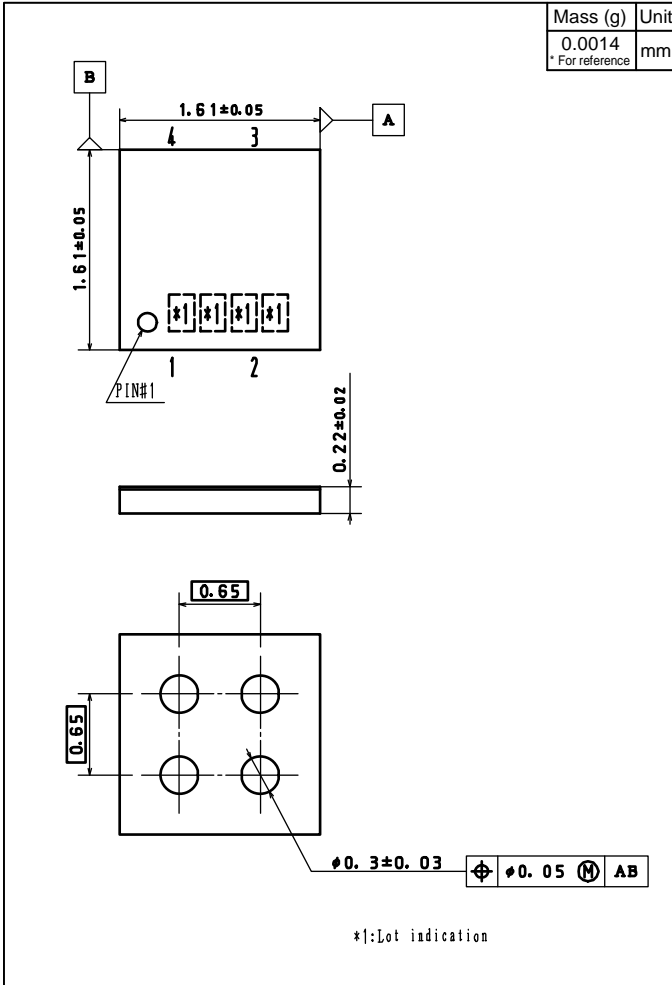


EFC4619R

Outline Drawing

EFC4619R-TR

Land Pattern Example



Note on usage : Since the EFC4619R is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

ON Semiconductor and the ON logo are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

[ON Semiconductor:](#)

[EFC4619R-TR](#)